

# MOSFET – Power, Single, P-Channel, $\mu$ 8FL

**-30 V, 7.5 m $\Omega$**

## NTTFS015P03P8Z

### Features

- Ultra Low  $R_{DS(on)}$  to Improve System Efficiency
- Advanced Package Technology in 3.3x3.3 mm for Space Saving and Excellent Thermal Conduction
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Typical Applications

- Power Load Switch
- Protection: Reverse Current, Over Voltage, and Reverse Negative Voltage
- Battery Management

### MAXIMUM RATINGS ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DSS}$	-30	V
Gate-to-Source Voltage	$V_{GS}$	$\pm 25$	V
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 2)	Steady State	$T_C = 25\text{ }^\circ\text{C}$	$I_D$ -47.6 A
		$T_C = 85\text{ }^\circ\text{C}$	-34.4
Power Dissipation $R_{\theta JC}$ (Notes 1, 2)	Steady State	$T_C = 25\text{ }^\circ\text{C}$	$P_D$ 33.8 W
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 25\text{ }^\circ\text{C}$	$I_D$ -13.4 A
		$T_A = 85\text{ }^\circ\text{C}$	-9.6
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 25\text{ }^\circ\text{C}$	$P_D$ 2.66 W
Pulsed Drain Current	$T_A = 25\text{ }^\circ\text{C}, t_p = 10\text{ }\mu\text{s}$	$I_{DM}$	-195 A
Operating Junction and Storage Temperature	$T_J, T_{stg}$	-55 to 150	$^\circ\text{C}$
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	$T_L$	260	$^\circ\text{C}$

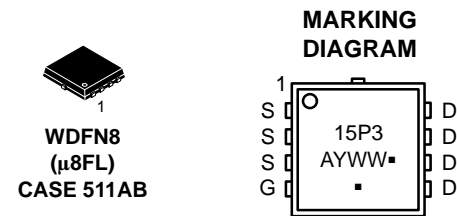
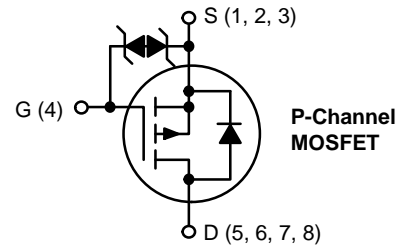
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Drain) (Note 2)	$R_{\theta JC}$	3.7	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	47	$^\circ\text{C}/\text{W}$

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 1 in<sup>2</sup>, 2 oz. Cu pad. Assuming a 76mm x 76mm x 1.6mm board.

$V_{(BR)DSS}$	$R_{DS(on)}$	$I_D$
-30 V	7.5 m $\Omega$ @ -10 V	-47.6 A
	12 m $\Omega$ @ -4.5 V	



15P3 = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NTTFS015P03P8ZTAG	WDFN8 (Pb-Free)	1500 / Tape & Reel
NTTFS015P03P8ZTWG	WDFN8 (Pb-Free)	3000 / Tape & Reel

<sup>†</sup> For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, [BRD8011/D](#).

# NTTFS015P03P8Z

## ELECTRICAL CHARACTERISTICS ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = -250\text{ }\mu\text{A}$ , ref to $25\text{ }^\circ\text{C}$		-4.4		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}, V_{DS} = -24\text{ V}$ $T_J = 25\text{ }^\circ\text{C}$			-1.0	$\mu\text{A}$
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 25\text{ V}$			$\pm 10$	$\mu\text{A}$

## ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250\text{ }\mu\text{A}$	-1.0		-3.0	V
Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	$I_D = -250\text{ }\mu\text{A}$ , ref to $25\text{ }^\circ\text{C}$		5.6		mV/ $^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -12\text{ A}$		5.0	7.5	m $\Omega$
		$V_{GS} = -4.5\text{ V}, I_D = -10\text{ A}$		8.0	12	
Forward Transconductance	$g_{FS}$	$V_{DS} = -5\text{ V}, I_D = -10\text{ A}$		77		S

## CHARGES AND CAPACITANCES

Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = -15\text{ V}$		2706		pF
Output Capacitance	$C_{oss}$			907		
Reverse Transfer Capacitance	$C_{rss}$			875		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -4.5\text{ V}, V_{DS} = -15\text{ V}, I_D = -10\text{ A}$		37		nC
Threshold Gate Charge	$Q_{G(TH)}$			5.1		
Gate-to-Source Charge	$Q_{GS}$			8.2		
Gate-to-Drain Charge	$Q_{GD}$			21.7		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -10\text{ V}, V_{DS} = -15\text{ V}, I_D = -10\text{ A}$		62.3	105	

## SWITCHING CHARACTERISTICS, $V_{GS} = 4.5\text{ V}$ (Note 3)

Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = -4.5\text{ V}, V_{DS} = -15\text{ V}, I_D = -10\text{ A}, R_G = 6\text{ }\Omega$		25		ns
Rise Time	$t_r$			138		
Turn-Off Delay Time	$t_{d(off)}$			55		
Fall Time	$t_f$			98		

## SWITCHING CHARACTERISTICS, $V_{GS} = 10\text{ V}$ (Note 3)

Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = -10\text{ V}, V_{DS} = -15\text{ V}, I_D = -10\text{ A}, R_G = 6\text{ }\Omega$		17		ns
Rise Time	$t_r$			34		
Turn-Off Delay Time	$t_{d(off)}$			99		
Fall Time	$t_f$			97		

## DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	$V_{SD}$	$V_{GS} = 0\text{ V}, I_S = -10\text{ A}$	$T_J = 25\text{ }^\circ\text{C}$		-0.8	-1.3	V
			$T_J = 125\text{ }^\circ\text{C}$		-0.65		
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0\text{ V}, di_S/dt = 100\text{ A}/\mu\text{s}, I_S = -10\text{ A}$		40.7		ns	
Charge Time	$t_a$			18.4			
Discharge Time	$t_b$			22.3			
Reverse Recovery Charge	$Q_{RR}$			29			nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

TYPICAL CHARACTERISTICS

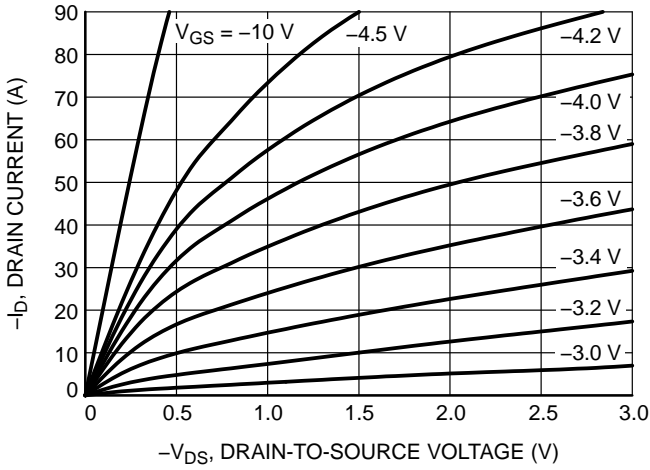


Figure 1. On-Region Characteristics

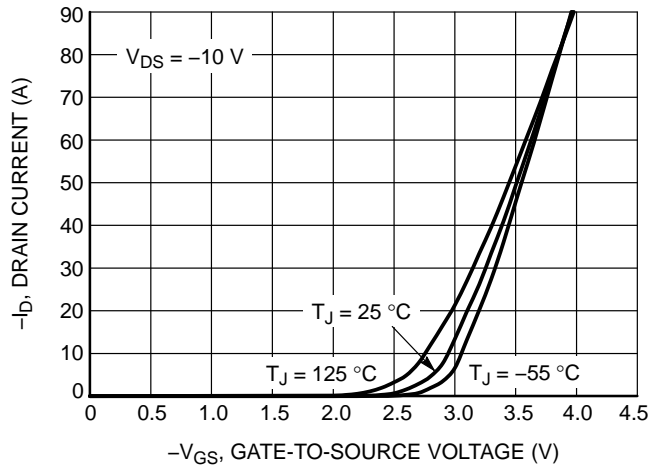


Figure 2. Transfer Characteristics

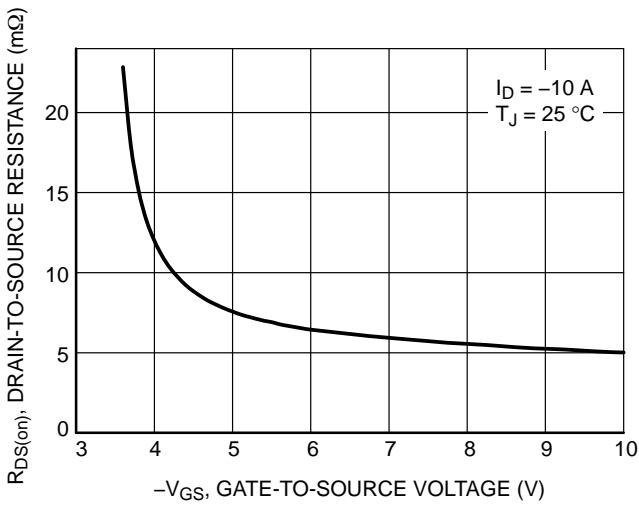


Figure 3. On-Resistance vs. Gate-to-Source Voltage

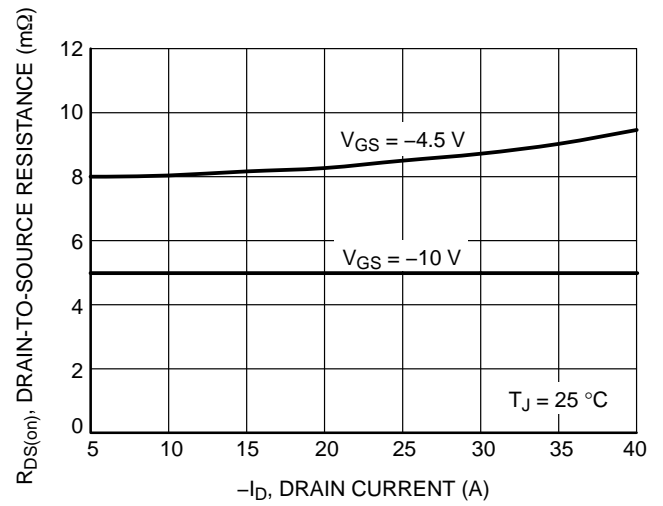


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

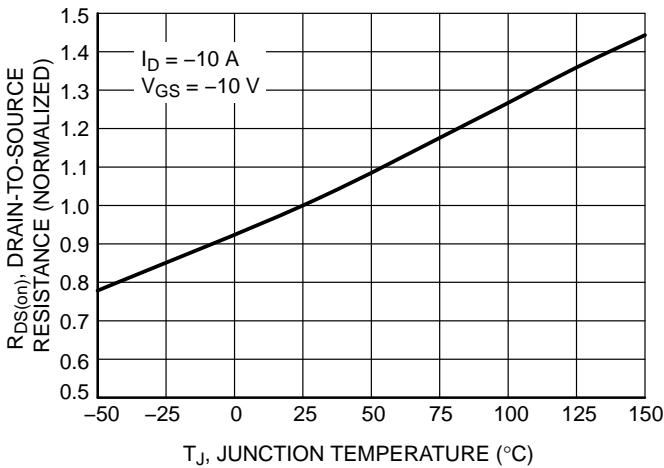


Figure 5. On-Resistance Variation with Temperature

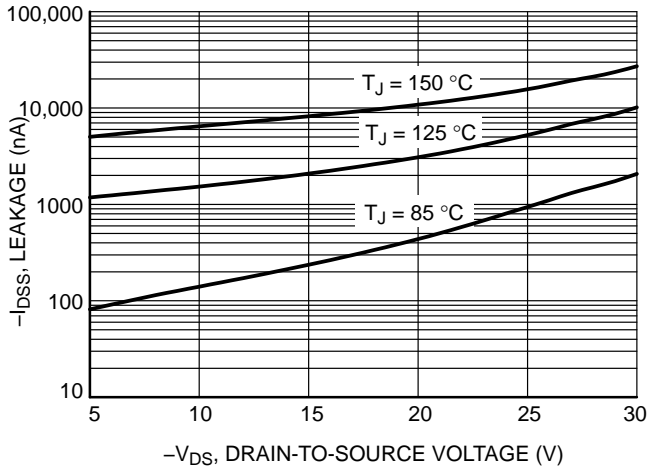


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

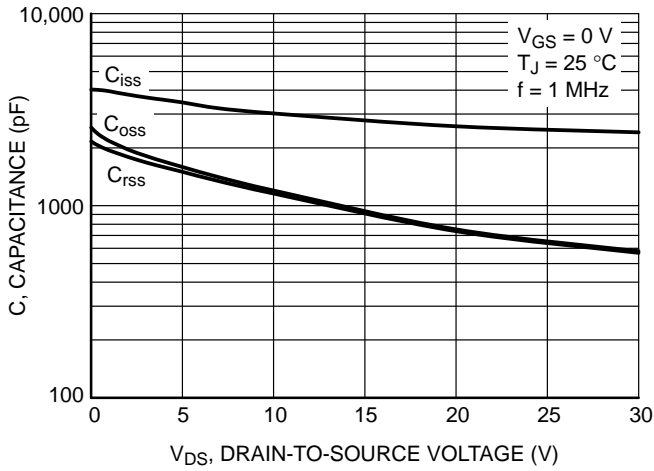


Figure 7. Capacitance Variation

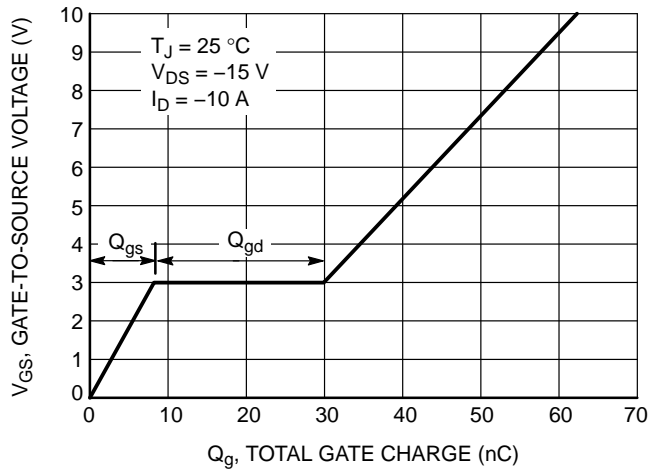


Figure 8. Gate-to-Source vs. Total Charge

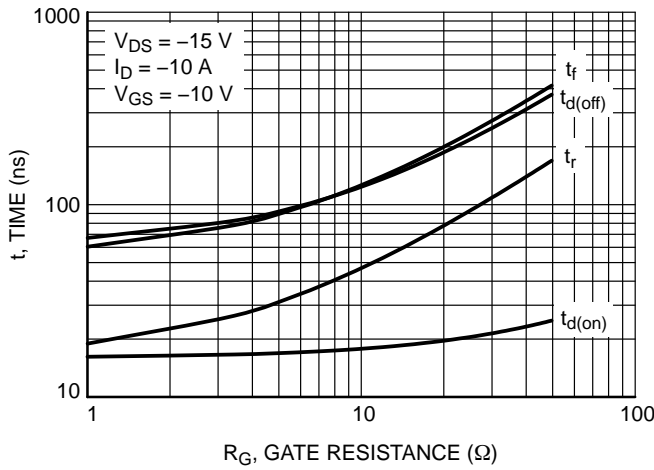


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

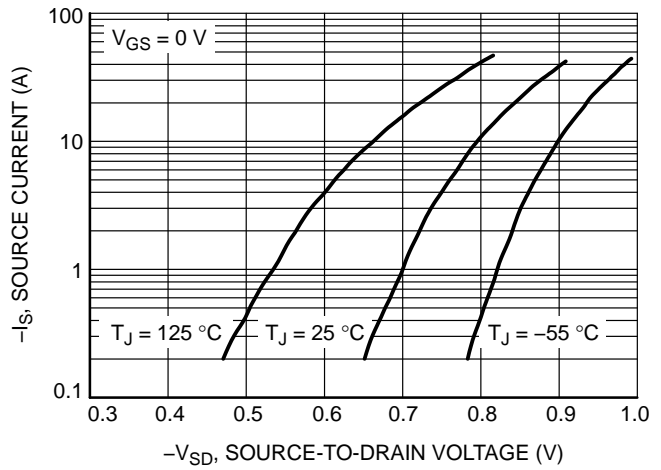


Figure 10. Diode Forward Voltage vs. Current

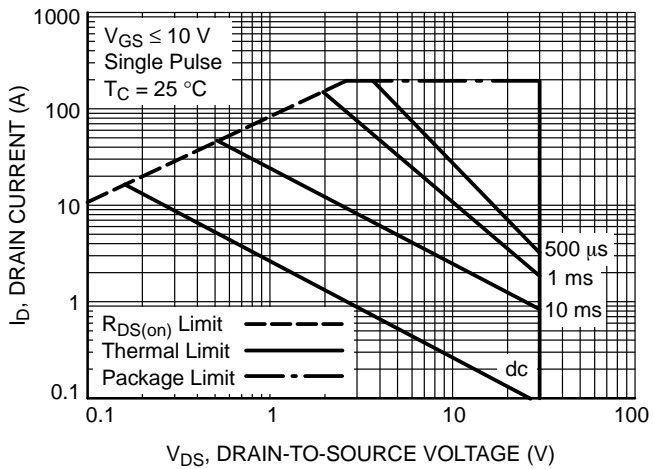


Figure 11. Maximum Rated Forward Biased Safe Operating Area

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## TYPICAL CHARACTERISTICS

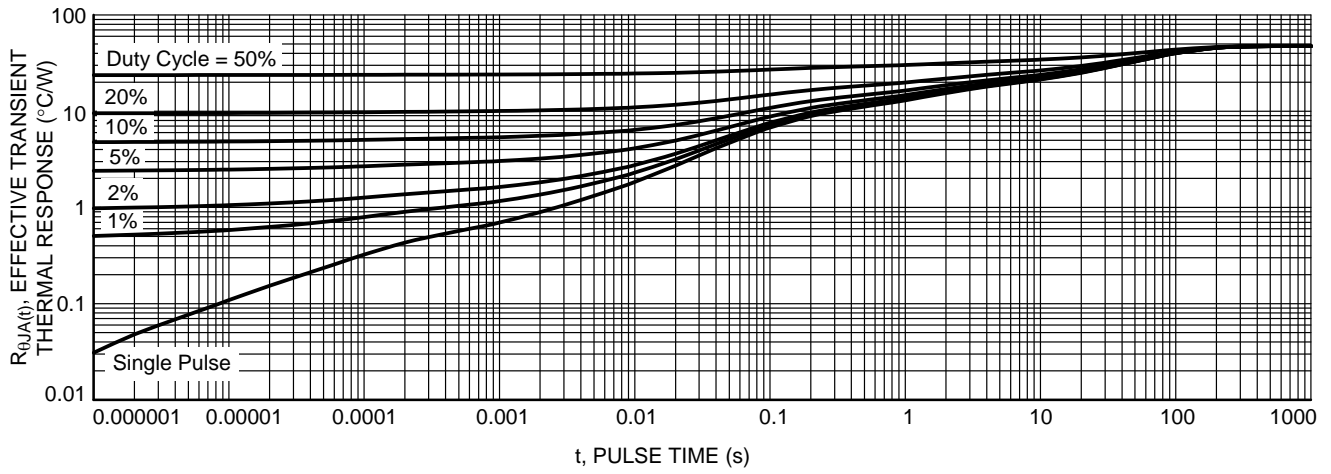


Figure 12. Thermal Response

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## REVISION HISTORY

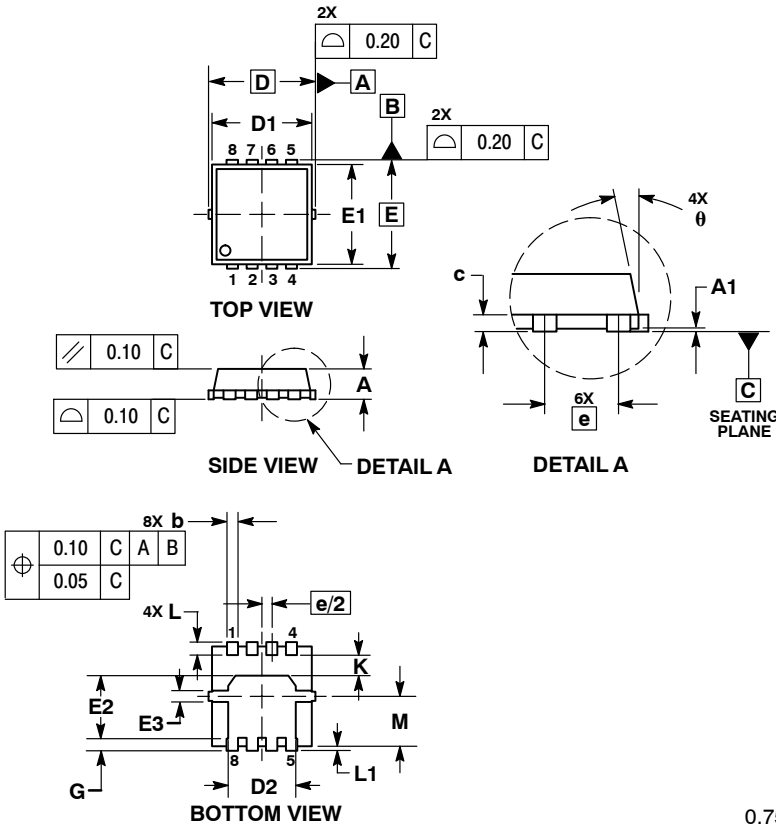
Revision	Description of Changes	Date
0	Initial Production Data Sheet release.	2/20/2019
1	Rebranded the Data Sheet to <b>onsemi</b> format.	10/20/2025



SCALE 2:1

WDFN8 3.3x3.3, 0.65P  
CASE 511AB  
ISSUE D

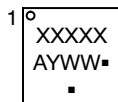
DATE 23 APR 2012



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.75	0.80	0.028	0.030	0.031
A1	0.00	---	0.05	0.000	---	0.002
b	0.23	0.30	0.40	0.009	0.012	0.016
c	0.15	0.20	0.25	0.006	0.008	0.010
D	3.30 BSC			0.130 BSC		
D1	2.95	3.05	3.15	0.116	0.120	0.124
D2	1.98	2.11	2.24	0.078	0.083	0.088
E	3.30 BSC			0.130 BSC		
E1	2.95	3.05	3.15	0.116	0.120	0.124
E2	1.47	1.60	1.73	0.058	0.063	0.068
E3	0.23	0.30	0.40	0.009	0.012	0.016
e	0.65 BSC			0.026 BSC		
G	0.30	0.41	0.51	0.012	0.016	0.020
K	0.65	0.80	0.95	0.026	0.032	0.037
L	0.30	0.43	0.56	0.012	0.017	0.022
L1	0.06	0.13	0.20	0.002	0.005	0.008
M	1.40	1.50	1.60	0.055	0.059	0.063
θ	0 °	---	12 °	0 °	---	12 °

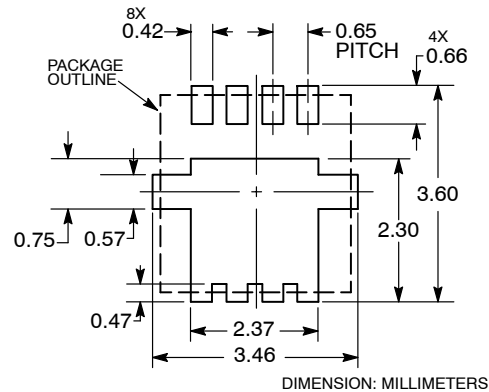
GENERIC MARKING DIAGRAM\*



- XXXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

SOLDERING FOOTPRINT\*



DIMENSION: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	WDFN8 3.3X3.3, 0.65P	PAGE 1 OF 1

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